



# Bipolar NPN Bare Die – BTN117

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## Part Description

The BTN117 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = 80V
- VCEO = 80V
- VEBO = 4V
- hFE = 90- @ VCE = 1V, IC = 0.01A
- VCE(Sat) = 0.33V @ IC = 0.1A, IB = 10mA
- fT = - MHz @ VCE = - V, IE = - A
- COBO = - pF @ VCB = - V

## Features

Low VCE(sat)

## Die Size (Unawn)

560µm X 560µm, 22 Mils X 22 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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